



FAST CMOS 16-BIT BIDIRECTIONAL 3.3V TO 5V TRANSLATOR

IDT74FCT164245T

FEATURES:

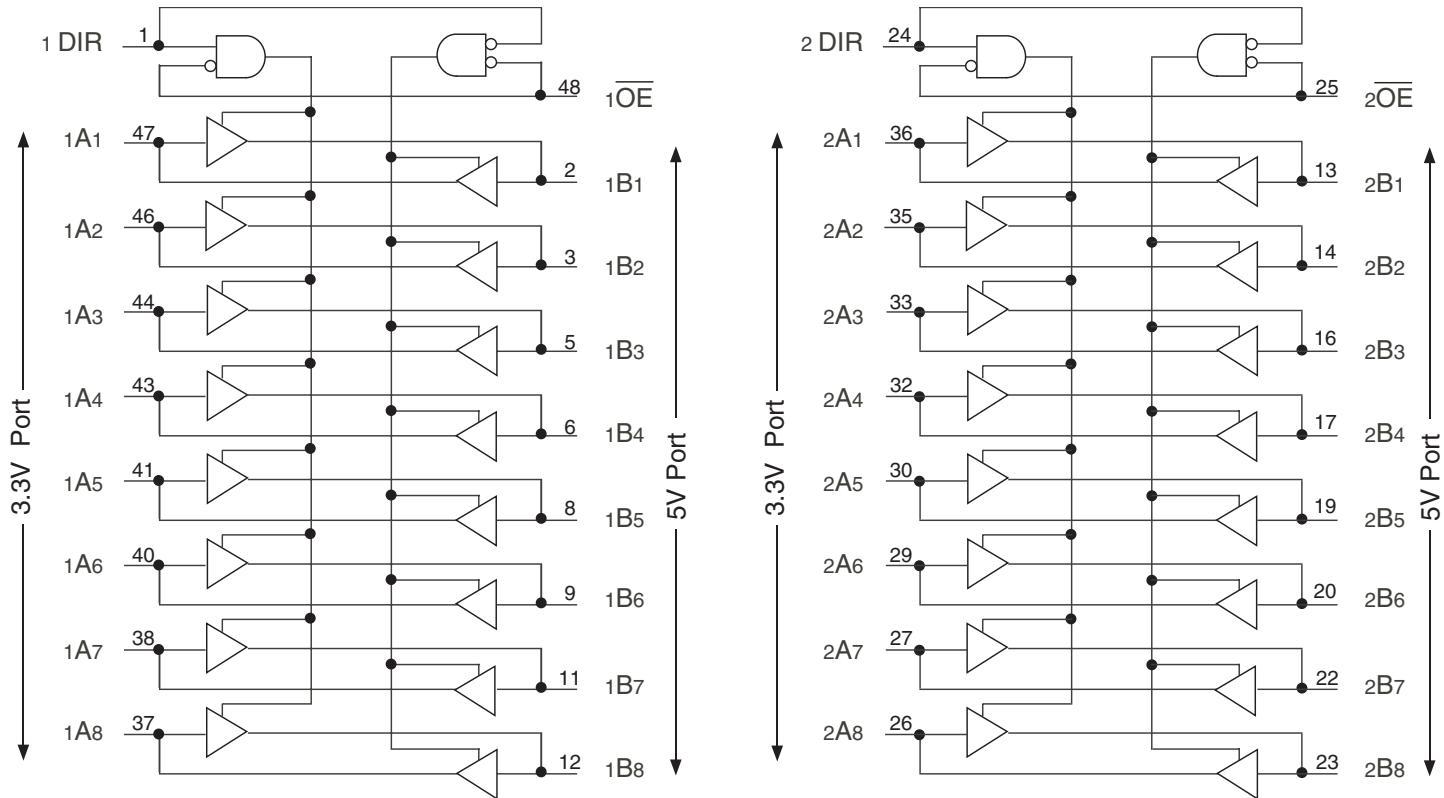
- 0.5 MICRON CMOS Technology
- Bidirectional interface between 3.3V and 5V buses
- Control inputs can be driven from either 3.3V or 5V circuits
- ESD > 2000V per MIL-STD-883, Method 3015; > 200V using machine model (C = 200pF, R = 0)
- V_{CC1} = 5V ±10%, V_{CC2} = 2.7V to 3.6V
- High drive outputs (-32mA I_{OH}, 64mA I_{OL}) on 5V port
- Power off disable on both ports permits "live insertion"
- Typical VOLP (Output Ground Bounce) < 0.9V at V_{CC1} = 5V, V_{CC2} = 3.3V, TA = 25°C
- Available in SSOP and TSSOP packages

DESCRIPTION:

The FCT164245T 16-bit 3.3V-to-5V translator is built using advanced dual metal CMOS technology. This high-speed, low-power transceiver is designed to interface between a 3.3V bus and a 5V bus in a mixed 3.3V/5V supply environment. This enables system designers to interface TTL compatible 3.3V components with 5V components. The direction and output enable controls operate these devices as either two independent 8-bit transceivers or one 16-bit transceiver. The A port interfaces with the 3.3V bus; the B port interfaces with the 5V bus. The direction control (xDIR) pin controls the direction of data flow. The output enable pin ($x\bar{OE}$) overrides the direction control and disables both ports. These control signals can be driven from either 3.3V or 5V devices.

The FCT164245T is ideally suited for driving high-capacitance loads and low-impedance backplanes. The output buffers are designed with power off disable capability to allow "hot insertion" of boards when used as backplane drivers. They also allow interface between a mixed supply system and external 5 volt peripherals.

FUNCTIONAL BLOCK DIAGRAM



The IDT logo is a registered trademark of Integrated Device Technology, Inc.

INDUSTRIAL TEMPERATURE RANGE

SEPTEMBER 2009

PIN CONFIGURATION

1DIR	1	48	1OE
1B1	2	47	1A1
1B2	3	46	1A2
GND	4	45	GND
1B3	5	44	1A3
1B4	6	43	1A4
VCC1	7	42	VCC2
1B5	8	41	1A5
1B6	9	40	1A6
GND	10	39	GND
1B7	11	38	1A7
1B8	12	37	1A8
2B1	13	36	2A1
2B2	14	35	2A2
GND	15	34	GND
2B3	16	33	2A3
2B4	17	32	2A4
VCC1	18	31	VCC2
2B5	19	30	2A5
2B6	20	29	2A6
GND	21	28	GND
2B7	22	27	2A7
2B8	23	26	2A8
2DIR	24	25	2OE

SSOP/ TSSOP
TOP VIEW**ABSOLUTE MAXIMUM RATINGS⁽¹⁾**

Symbol	Description	Max	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7	V
VTERM ⁽³⁾	Terminal Voltage with Respect to GND	-0.5 to Vcc1+0.5	V
TA	Operating Temperature	-40 to +85	°C
TBIAS	Temperature Under Bias	-55 to +125	°C
TSTG	Storage Temperature	-55 to +125	°C
PT	Power Dissipation	1	W
IOUT	DC Output Current	-60 to +120	mA

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- All devices except Vcc2.
- Power supply terminal Vcc2.

CAPACITANCE (TA = +25°C, F = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Typ.	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	3.5	6	pF
C _{I/O}	I/O Capacitance	V _{OUT} = 0V	3.5	8	pF

NOTE:

- This parameter is measured at characterization but not tested.

PIN DESCRIPTION

Pin Names	Description	
xOE	Output Enable Input (Active LOW)	
xDIR	Direction Control Input	
xAx	Side A Inputs or 3-State Outputs (3.3V Port)	
xBx	Side B Inputs or 3-State Outputs (5V Port)	

FUNCTION TABLE⁽¹⁾

Inputs		Outputs
xOE	xDIR	
L	L	Bus B Data to Bus A
L	H	Bus A Data to Bus B
H	X	High Z State

NOTE:

- H = HIGH Voltage Level
- L = LOW Voltage Level
- X = Don't Care
- Z = High-Impedance

POWER SUPPLY SEQUENCING

In the 74FCT164245T, the condition of $V_{CC1} \geq (V_{CC2} - 0.5V)$ must be maintained at all times. For the range of $V_{CC1} = (V_{CC2} - 0.5V)$ to $V_{CC1} = (V_{CC2} + 0.9V)$, both the A and B ports will remain in a High-Impedance state.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE (A PORT, 3.3V)

Following Conditions Apply Unless Otherwise Specified:

V_{CC1} = 5V ±10%, V_{CC2} = 2.7V to 3.6V, Industrial: TA = -40°C to +85°C

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
V _{IH}	Input HIGH Level (Input and I/O pins)	Guaranteed Logic HIGH Level		2	—	5.5	V
V _{IL}	Input LOW Level (Input and I/O pins)	Guaranteed Logic LOW Level		-0.5	—	0.8	V
I _{IH}	Input HIGH Current (Input pins)	V _{CC1} = Max. V _{CC2} = Max.	V _I = 5.5V	—	—	±5	µA
	Input HIGH Current (I/O pins)		V _I = V _{CC2}	—	—	±15	
I _{IL}	Input LOW Current (Input pins)		V _I = GND	—	—	±5	
	Input LOW Current (I/O pins)		V _I = GND	—	—	±15	
V _{IK}	Clamp Diode Voltage	V _{CC2} = Min., I _{IN} = -18mA		—	-0.7	-1.2	V
V _{OH}	Output HIGH Voltage	V _{CC1} = V _{CC2} = Min. V _{IN} = V _{IH} or V _{IL}	I _{OH} = -0.1mA	V _{CC2} = 0.2	—	—	V
		V _{CC2} = 3V V _{IN} = V _{IH} or V _{IL}	I _{OH} = -8mA	2.4	3	—	
V _{OL}	Output LOW Voltage	V _{CC1} = Min. V _{CC2} = Min. V _{IN} = V _{IH} or V _{IL}	I _{OL} = 0.1mA I _{OL} = 16mA I _{OL} = 24mA	—	—	0.2	V
		V _{CC} = 3V V _{IN} = V _{IH} or V _{IL}	I _{OL} = 24mA	—	0.3	0.55	
				—	0.3	0.5	
				—	—	—	
I _{OFF}	Input/Output Power Off Leakage	V _{CC1} = 0V, V _{CC2} = 0V, V _{IN} or V _O ≤ 4.5V		—	—	±100	µA
I _{os}	Short Circuit Current ⁽⁴⁾	V _{CC1} = Max., V _{CC2} = Max., V _O = GND ⁽³⁾		-70	-105	-150	mA
I _o	Output Drive Current	V _{CC1} = Max., V _{CC2} = Max., V _O = 1.5V ⁽³⁾		-40	-60	-90	mA
V _H	Input Hysteresis	—		—	150	—	mV
I _{CC2}	Quiescent Power Supply Current	V _{CC1} = Max. V _{CC2} = Max. V _{IN} = GND or V _{CC2}		—	0.35	2	mA
I _{CC2H}				—	—	—	—
I _{CC2Z}				—	—	—	—

NOTES:

1. For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.

2. Typical values are at V_{CC1} = 5V, V_{CC2} = 3.3V, +25°C ambient.

3. Not more than one output should be shorted at one time. Duration of the test should not exceed one second.

4. This parameter is guaranteed but not tested.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE (B PORT, 5V)

Following Conditions Apply Unless Otherwise Specified:

V_{CC1} = 5V ±10%, V_{CC2} = 2.7V to 3.6V, Industrial: TA = -40°C to +85°C

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
V _{IH}	Input HIGH Level (Input and I/O pins)	Guaranteed Logic HIGH Level		2	—	5.5	V
V _{IL}	Input LOW Level (Input and I/O pins)	Guaranteed Logic LOW Level		-0.5	—	0.8	V
I _{IH}	Input HIGH Current (Input pins)	V _{CC1} = Max. V _{CC2} = Max.	V _I = V _{CC1}	—	—	±5	μA
	Input HIGH Current (I/O pins)			—	—	±15	
I _{IL}	Input LOW Current (Input pins)		V _I = GND	—	—	±5	
	Input LOW Current (I/O pins)			—	—	±15	
V _{IK}	Clamp Diode Voltage	V _{CC1} = Min., I _{IN} = -18mA		—	-0.7	-1.2	V
V _{OH}	Output HIGH Voltage	V _{CC1} = Min. V _{CC2} = Min. V _{IN} = V _{IH} or V _{IL}	I _{OH} = -3mA	2.5	3.5	—	V
			I _{OH} = -15mA	2.4	3.5	—	
			I _{OH} = -32mA ⁽⁵⁾	2	3	—	
V _{OL}	Output LOW Voltage	V _{CC1} = Min. V _{CC2} = Min. V _{IN} = V _{IH} or V _{IL}	I _{OL} = 64mA	—	0.2	0.55	V
I _{OFF}	Input/Output Power Off Leakage	V _{CC1} = 0V, V _{CC2} = 0V, V _{IN} or V _O ≤ 4.5V		—	—	±100	μA
I _{os}	Short Circuit Current ⁽⁴⁾	V _{CC1} = Max., V _{CC2} = Max., V _O = GND ⁽³⁾		-80	-140	-225	mA
I _o	Output Drive Current	V _{CC1} = Max., V _{CC2} = Max., V _O = 2.5V ⁽³⁾		-50	-75	-180	mA
V _H	Input Hysteresis	—		—	150	—	mV
I _{CC2} I _{CC2H} I _{CC2Z}	Quiescent Power Supply Current	V _{CC1} = Max. V _{CC2} = Max. V _{IN} = GND or V _{CC2}		—	0.08	1.5	mA

NOTES:

1. For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.
2. Typical values are at V_{CC1} = 5V, V_{CC2} = 3.3V, +25°C ambient.
3. Not more than one output should be shorted at one time. Duration of the test should not exceed one second.
4. This parameter is guaranteed but not tested.
5. Duration of the condition cannot exceed one second.

POWER SUPPLY CHARACTERISTICS

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
ΔI_{CC}	Quiescent Power Supply Current TTL Inputs HIGH	$V_{CC1} = \text{Max.}, V_{CC2} = \text{Max.}$ $V_{IN} = V_{CC2} - 0.6V^{(3)}$		—	12	30	μA
I_{CCD}	Dynamic Power Supply Current ⁽⁴⁾	$V_{CC1} = \text{Max.}, V_{CC2} = \text{Max.}$ Outputs Open $x_{OE} = x_{DIR} = GND$ One Input Toggling 50% Duty Cycle	$V_{IN} = V_{CC2}$ $V_{IN} = GND$	—	75	120	$\mu A / MHz$
I_C	Total Power Supply Current ⁽⁶⁾	$V_{CC1} = \text{Max.}, V_{CC2} = \text{Max.}$ Outputs Open $f_i = 10MHz$ 50% Duty Cycle $x_{OE} = x_{DIR} = GND$ One Bit Toggling	$V_{IN} = V_{CC2} - 0.6V$ $V_{IN} = GND$	—	1.2	4.7	mA
		$V_{CC1} = \text{Max.}, V_{CC2} = \text{Max.}$ Outputs Open $f_i = 2.5MHz$ 50% Duty Cycle $x_{OE} = x_{DIR} = GND$ Sixteen Bits Toggling	$V_{IN} = V_{CC2} - 0.6V$ $V_{IN} = GND$	—	3.5	8.5 ⁽⁵⁾	

NOTES:

1. For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.

2. Typical values are at $V_{CC1} = 5V$, $V_{CC2} = 3.3V$, $+25^\circ C$ ambient.

3. Per TTL driven input. All other inputs at V_{CC} or GND .

4. This parameter is not directly testable, but is derived for use in Total Power Supply Calculations.

5. Values for these conditions are examples of the I_C formula. These limits are guaranteed but not tested.

6. $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$

$$I_C = I_{CC1} + I_{CC2} + \Delta I_{CC} D_{HNT} + I_{CCD} (f_{CP} N_{CP}/2 + f_i N_i)$$

I_{CC1} = Quiescent Current (I_{CC1L} , I_{CC1H} and I_{CC1Z})

I_{CC2} = Quiescent Current (I_{CC2L} , I_{CC2H} and I_{CC2Z})

ΔI_{CC} = Power Supply Current for a TTL High Input

D_H = Duty Cycle for TTL Inputs High

N_T = Number of TTL Inputs at D_H

I_{CCD} = Dynamic Current caused by an Input Transition Pair (HLH or LHL)

f_{CP} = Clock Frequency for Register Devices (Zero for Non-Register Devices)

N_{CP} = Number of Clock Inputs at f_{CP}

f_i = Input Frequency

N_i = Number of Inputs at f_i

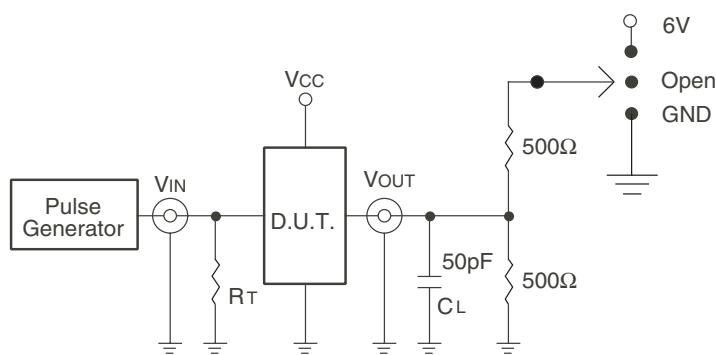
SWITCHING CHARACTERISTICS OVER OPERATING RANGE⁽¹⁾

Symbol	Parameter	Condition ⁽¹⁾	Min. ⁽²⁾	Max.	Unit
t _{PLH}	Propagation Delay A to B	CL = 50pF RL = 500Ω	1.5	5	ns
t _{PHL}	Propagation Delay B to A		1.5	5	ns
t _{PZH}	Output Enable Time x _O E to B		1.5	6.5	ns
t _{PZL}	Output Disable Time x _O E to B		1.5	6	ns
t _{PHZ}	Output Enable Time x _O E to A		1.5	6.5	ns
t _{PZL}	Output Disable Time x _O E to A		1.5	6	ns
t _{PZH}	Output Enable Time xDIR to B ⁽³⁾		1.5	6.5	ns
t _{PZL}	Output Disable Time xDIR to B ⁽³⁾		1.5	6	ns
t _{PHZ}	Output Enable Time xDIR to A ⁽³⁾		1.5	6.5	ns
t _{PZL}	Output Disable Time xDIR to A ⁽³⁾		1.5	6	ns

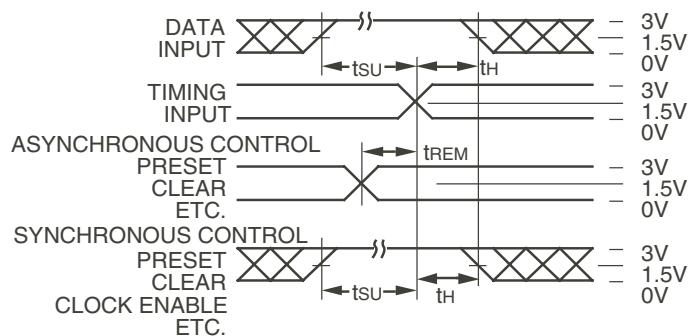
NOTES:

1. See test circuit and waveforms.
2. Minimum limits are guaranteed but not tested on Propagation Delays.
3. This parameter is guaranteed but not tested.

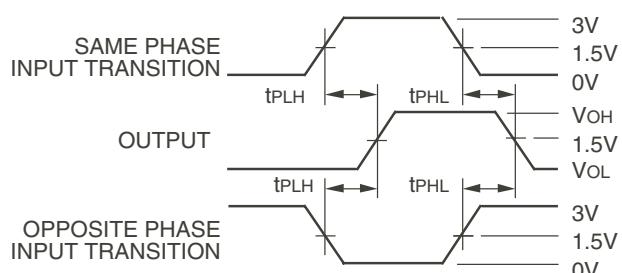
TEST CIRCUITS AND WAVEFORMS



Test Circuits for All Outputs



Set-up, Hold, and Release Times



Propagation Delay

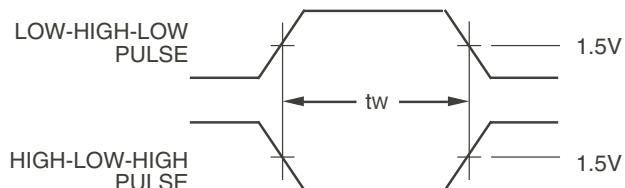
SWITCH POSITION

Test	Switch
Open Drain	
Disable Low	6V
Enable Low	
Disable High	GND
Enable High	
All Other Tests	Open

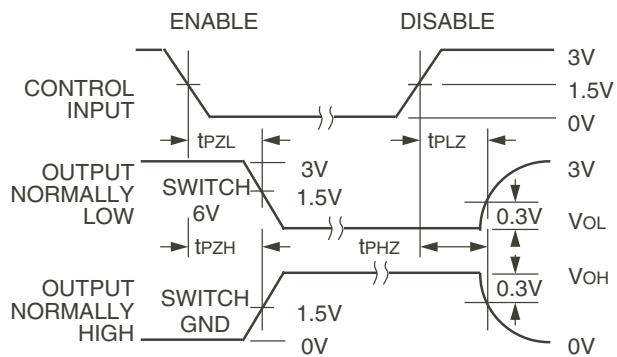
DEFINITIONS:

CL = Load capacitance: includes jig and probe capacitance.

RT = Termination resistance: should be equal to ZOUT of the Pulse Generator.



Pulse Width



Enable and Disable Times

NOTES:

1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.
2. Pulse Generator for All Pulses: Rate $\leq 1.0\text{MHz}$; $t_f \leq 2.5\text{ns}$; $t_r \leq 2.5\text{ns}$.

ORDERING INFORMATION

XX	FCT	XX	XXXX	X	
Temp. Range	Family	Device Type	Package		
				PVG	Shrink Small Outline Package - Green
				PAG	Thin Shrink Small Outline Package - Green
			245T		16-Bit Bidirectional 3.3 Volt to 5 Volt Translator
			164		Double-Density
			74		40 C to +85 C

Datasheet Document History

09/28/09 Pg. 8

Updated the ordering information by removing the "IDT" notation and non RoHS part.



CORPORATE HEADQUARTERS
 6024 Silver Creek Valley Road
 San Jose, CA 95138

for SALES:
 800-345-7015 or 408-284-8200
 fax: 408-284-2775
www.idt.com

for Tech Support:
logichelp@idt.com